INTERNATIONAL STANDARD

ISO 22278

First edition
2020-08

Fine ceramics (advanced ceramics, advanced technical ceramics) — Test method for crystalline quality of single-crystal thin film (wafer) using XRD method with parallel X-ray beam

Reference number
ISO 22278:2020(E)

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ISO copyright office
CP 401 • Ch. de Blandonnet 8
CH-1214 Vernier, Geneva
Phone: +41 22 749 01 11
Email: copyright@iso.org
Website: www.iso.org

Published in Switzerland

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